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**IN THE CLAIMS:**

Please amend claims 11 and 15 and add new claims 19-21 as follows.

1.-10. (Canceled)

11. (Currently amended) An RF device comprising:

a plurality of semiconductor elements formed on a semiconductor substrate

composed of a semiconductor material;

a plurality of through holes which are provided between two adjacent ones of the plurality of semiconductor elements and pass from a surface through the backside of the semiconductor substrate,

wherein a distance between two adjacent ones of the plurality of through holes is smaller than a thickness of the semiconductor substrate so as to reduce power leaking between two adjacent ones of the plurality of semiconductor elements.

12. (Previously Presented) The device of claim 11, wherein side faces of the plurality of through holes are covered with a conductive material.

13. (Previously Presented) The device of claim 12, wherein the conductive material is electrically connected to a ground wiring layer provided on the surface of the backside of the semiconductor substrate.

14. (Previously Presented) The device of claim 11, wherein the semiconductor substrate is a GaAs substrate.

15. (Currently amended) An RF device comprising:

a plurality of semiconductor elements formed on a semiconductor substrate

composed of a semiconductor material;

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a first group of through holes which are provided between two adjacent ones of the plurality of semiconductor elements and pass from a surface through the backside of the semiconductor substrate and whose side faces are covered with a conductive material; and

a second group of through holes which are provided in electrodes of the plurality of semiconductor elements, pass from a surface through the backside of the semiconductor substrate, and whose side faces are covered with the conductive material,

wherein the conductive material which covers side faces of the first and second groups of through holes is electrically connected to a first wiring layer provided on the backside of the semiconductor substrate, and

a distance between two adjacent ones of the first group of through holes is smaller than a thickness of the semiconductor substrate so as to reduce power leaking between two adjacent ones of the plurality of semiconductor elements.

16. (Previously Presented) The device of claim 15, wherein the semiconductor substrate is a GaAs substrate.

17. (Previously Presented) The RF device of claim 11, wherein the distance between two adjacent ones of the plurality of through holes is smaller than a thickness of the semiconductor substrate so as to exponentially reduce power leaking between two adjacent ones of the plurality of semiconductor elements with regard to the distance between two adjacent ones of the plurality of through holes.

18. (Previously Presented) The RF device of claim 15, wherein the distance between two adjacent ones of the first group of through holes is smaller than a thickness of the semiconductor substrate so as to exponentially reduce

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power leaking between two adjacent ones of the plurality of semiconductor elements with regard to the distance between two adjacent ones of the first group of through holes.

19. (New) The RF device of claim 15,

wherein some through holes of the first group and some through holes of the second group are electrically connected to the first wiring layer, and

some of the other through holes of the first group and some of the other through holes of the second group are electrically connected to a second wiring layer.

20. (New) The RF device of claim 19,

wherein a grounded wiring layer is formed on a printed circuit board, and

the first and second wiring layers are electrically connected to the grounded wiring layer.

21. (New) The RF device of claim 20,

wherein a third wiring layer other than the grounded wiring layer is formed on the printed circuit board, and

one of the through holes of the second group is electrically connected to the third wiring layer.